



EFW/Receipt

DOCKET NO.: 252311US2S/sma

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

GROUP: 2811

Syotaro ONO, et al.

SERIAL NO: 10/829,173

ATTENTION:

FILING RECEIPT CORRECTIONS

FILED: April 22, 2004

FOR: SEMICONDUCTOR DEVICE HAVING VERTICAL MOS GATE
STRUCTURE AND METHOD OF MANUFACTURING THE SAME

REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

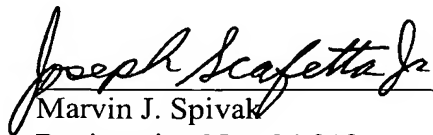
Office of Initial Patent Examination
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The Patent Office is requested to provide a corrected Official Filing Receipt for the attached. No fees are required. If you have any questions, please do not hesitate to contact us.

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Marvin J. Spivak
Registration No. 24,913

Joseph Scafetta, Jr.
Registration No. 26,803

Customer Number

22850

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/04)



UNITED STATES PATENT AND TRADEMARK OFFICE

NOV 23 2004

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/829,173	04/22/2004	2811	900	252311US2S	4	18	3

22850
OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C.
1940 DUKE STREET
ALEXANDRIA, VA 22314

CONFIRMATION NO. 6045
UPDATED FILING RECEIPT



OC000000013927555

Date Mailed: 09/29/2004

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Syotaro Ono, Yokohama-shi, JAPAN;
Yusuke Kawaguchi, Miura-gun, JAPAN;
Akio Nakagawa, Fujisawa-shi, JAPAN;

Power of Attorney: The patent practitioners associated with Customer Number 22850.

Domestic Priority data as claimed by applicant

Foreign Applications

JAPAN 2003-118462 04/23/2003

If Required, Foreign Filing License Granted: 07/07/2004

The number of your priority application, to be used for filing abroad under the Paris Convention is,
US10/829,173

Projected Publication Date: 01/06/2005

Non-Publication Request: No

Early Publication Request: No

RECEIVED: 9129104
OBLON, SPIVAK, McCLELLAND
MAIER & NEUSTADT, P.C.

DOCKETING DEPT.
Initials/Date Docketed: PP 9129104
Type of Resp(s): _____
Due Date(s): _____

Title

Semiconductor device having verical MOS gate structure and method of manufacturing the same

Preliminary Class

257

PLEASE NOTE THAT THE TITLE IS INCORECT. IT SHOULD READ AS FOLLOWS:

SEMICONDUCTOR DEVICE HAVING VERTICAL MOS GATE STRUCTURE AND
METHOD OF MANUFACTURING THE SAME